

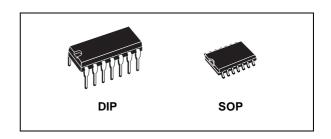


8 INPUT NAND/AND GATE

- MEDIUM-SPEED OPERATION t_{PHL}, t_{PLH} = 75ns (Typ.) at 10V
- BUFFERED OUTPUT
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



The HCF4068B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4068B 8 INPUT NAND/AND GATE provide the system designer with direct

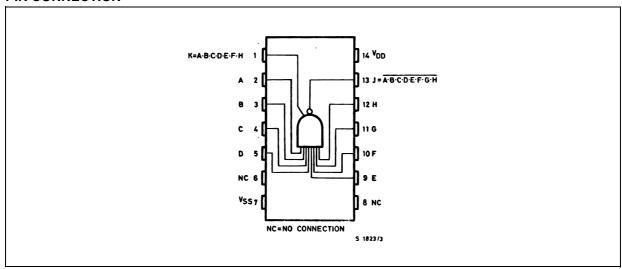


ORDER CODES

PACKAGE	TUBE	T&R			
DIP	HCF4068BEY				
SOP	HCF4068BM1	HCF4068M013TR			

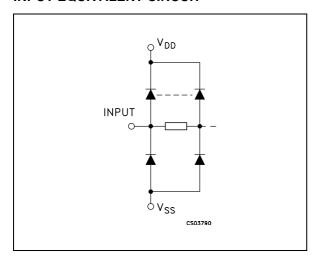
implementation of the positive-logic 8-input NAND and AND functions and supplements the existing family of CMOS gates.

PIN CONNECTION



September 2001 1/8

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 3, 4, 5, 9, 10, 11, 12	A, B, C, D, E, F, G, H	Data Inputs
6, 8	NC	Not Connected
1	K	Data Output (AND)
13	J	Data Output (NAND)
7	V_{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

TRUTH TABLES

		OUTPUT						
Α	В	С	D	Е	F	G	Н	J (NAND)
L	Х	Χ	Х	Х	Х	Х	Χ	Н
Х	L	Χ	Χ	Х	Χ	Χ	Χ	Н
Х	Х	L	Х	Х	Χ	Χ	Х	Н
Х	Х	Χ	L	Х	Χ	Χ	Χ	Н
Х	Х	Χ	Х	L	Х	Χ	Χ	Н
Х	Х	Χ	Χ	Х	L	Χ	Χ	Н
Х	Х	Χ	Χ	Х	Χ	L	Χ	Н
Х	Х	Χ	Х	Х	Х	Х	L	Н
Н	Н	Η	Η	Н	Η	Η	Η	Ĺ

			INP	UTS				OUTPUT
Α	В	С	D	Е	F	G	Н	K (AND)
L	Χ	Х	Х	Х	Х	Х	Х	L
Χ	L	Х	Х	Х	Х	Х	Х	L
Χ	Χ	L	Χ	Χ	Х	Х	Χ	L
Χ	Χ	Χ	L	Χ	Х	Х	Χ	L
Χ	Χ	Х	Χ	L	Х	Х	Х	L
Χ	Χ	Χ	Χ	Χ	L	Х	Χ	L
Χ	Χ	Χ	Χ	Х	Х	L	Х	L
Χ	Χ	Х	Χ	Х	Х	Х	L	L
Н	Ι	Н	Ι	Η	Н	Н	Η	Н

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

		Test Condition				Value							
Symbol	Parameter	Vı	v _o	ΙΙ _Ο Ι	V _{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(μ A)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	
		0/10			10		0.01	0.5		15		15	^
		0/15			15		0.01	1		30		30	μΑ
		0/20			20		0.02	5		150		150	
V _{OH}	High Level Output	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Low Level Output	5/0		<1	5		0.05			0.05		0.05	
	Voltage	10/0		<1	10		0.05			0.05		0.05	V
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input		0.5/4.5	<1	5	3.5			3.5		3.5		
	Voltage		1/9	<1	10	7			7		7		V
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input		4.5/0.5	<1	5			1.5		1.5		1.5	
	Voltage		9/1	<1	10			3		3		3	V
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		
	Current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mΑ
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		IIIA
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I _{OL}	Output Sink	0/5	0.4	<1	5	0.44	1		0.36		0.36		
	Current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
lı	Input Leakage Current	0/18	Any In	put	18		±10 ⁻⁵	±0.1		±1		±1	μΑ
C _I	Input Capacitance		Any In	put			5	7.5					pF

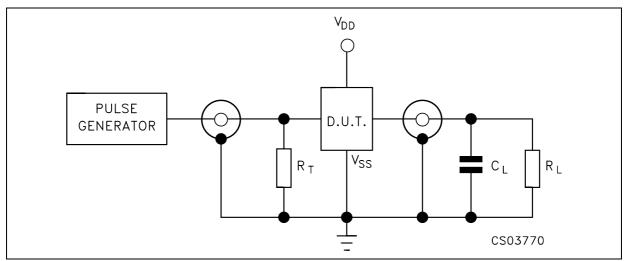
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} =5V, 2V min. with V_{DD} =10V, 2.5V min. with V_{DD} =15V

$\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \; (T_{amb} = 25^{\circ}C, \;\; C_{L} = 50 \text{pF}, \; R_{L} = 200 \text{K}\Omega, \;\; t_{r} = t_{f} = 20 \; \text{ns})$

Cumbal	Davamatar		Test Condition	'	Value (*)			
Symbol	Parameter	V _{DD} (V)		Min.	Тур.	Max.		
t _{PLH} t _{PHL}	Propagation Delay Time	5			150	300		
		10			75	150	ns	
		15			55	110		
t _{TLH} t _{THL}	Output Transition Time	5			100	200		
		10			50	100	ns	
		15			40	80	ĺ	

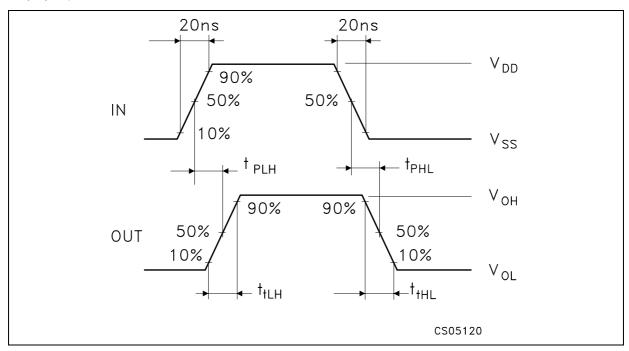
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT

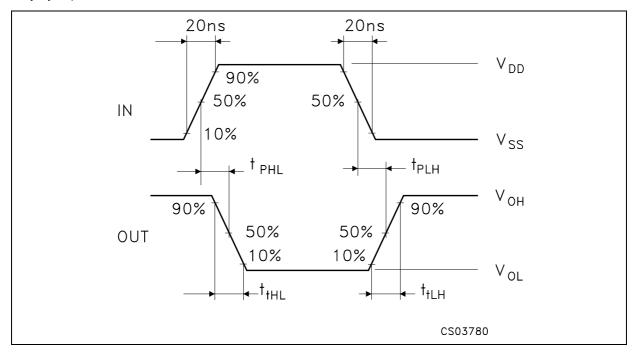


 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200K Ω R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM 1: PROPAGATION DELAY TIMES FOR K OUTPUT (AND FUNCTION) (f=1MHz; 50% duty cycle)

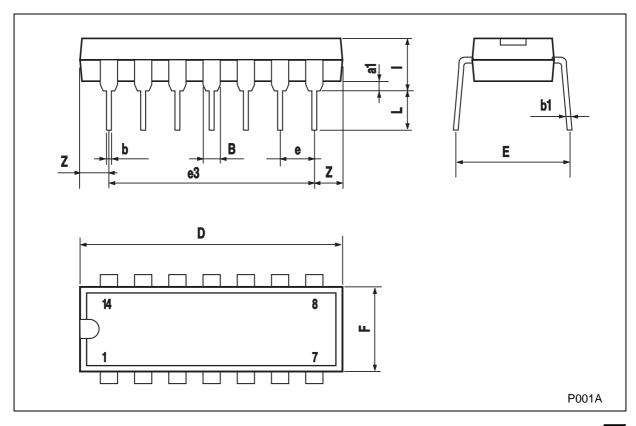


WAVEFORM 2 : PROPAGATION DELAY TIMES FOR J OUTPUT (NAND FUNCTION)(f=1MHz; 50% duty cycle)



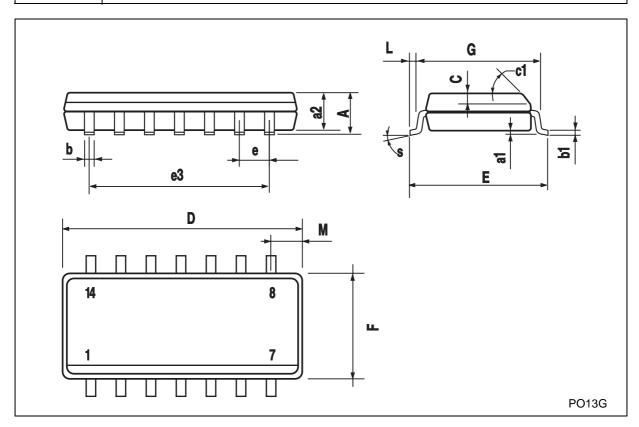
Plastic DIP-14 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
Е		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
1			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



SO-14 MECHANICAL DATA

DIM.		mm.		inch				
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)	•			
D	8.55		8.75	0.336		0.344		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S		!	8° (r	nax.)	•	!		



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